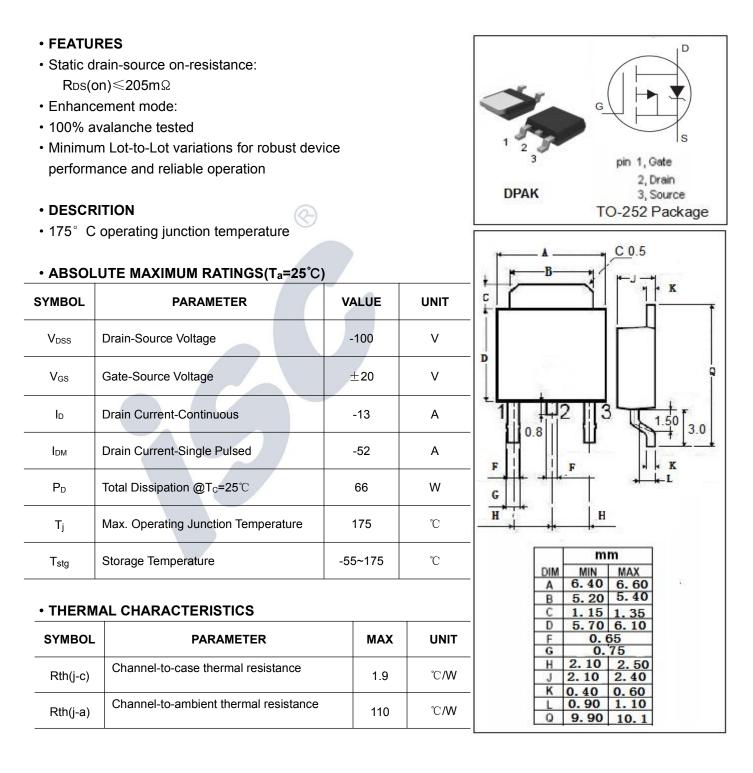


isc P-Channel MOSFET Transistor

IRFR5410,IIRFR5410





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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = -0.25mA	-100			V
V _{GS(th)}	Gate Threshold Voltage	VDS=VGS; I _D = -0.25mA	-2		-4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = -10V; I _D = -7.8A			205	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = -100V; V _{GS} = 0V			-25	μA
V _{SD}	Diode forward voltage	I _S = -7.8A, V _{GS} = 0V			-1.6	V

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